

IRF7811AVTRPBF

IRF7811AVTRPBF Information



For Reference Only

Part Number IRF7811AVTRPBF **Manufacturer** Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 10.8A 8-SOIC **Package** 8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF7811AVTRPBF Specifications

Manufacturer Part Number IRF7811AVTRPBF Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 10.8A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 26nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1801pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 14 mOhm @ 15A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)		
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FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 10.8A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 26nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1801pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 14 mOhm @ 15A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Package	8-SOIC (0.154", 3.90mm Width)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C10.8A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs26nC @ 5VInput Capacitance (Ciss) (Max) @ Vds1801pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs14 mOhm @ 15A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Series	HEXFET?
Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C10.8A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs26nC @ 5VInput Capacitance (Ciss) (Max) @ Vds1801pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs14 mOhm @ 15A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 4.5V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **ET Feature** Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 15A, 4.5V Operating Temperature Supplier Device Package Package / Case 10.8A (Ta) 10.8C (Ta) 10.8A (Ta) 10.8C (Ta) 10.8A (Ta) 10.8C (Ta) 10.8A (Ta) 10.8C	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Surplier Device Package Package / Case 4.5V 3V @ 250μA 4.5V	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Surplier Device Package Package / Case 3V @ 250μA 26nC @ 5V 1801pF @ 10V 25V 1801pF @ 10V 2.5W (Ta) 14mOhm @ 15A, 4.5V Cys (TJ) Surface Mount Surface Mount 8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	10.8A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature For Temperature Coperating Temperature Surface Mount Supplier Device Package Package / Case 26nC @ 5V 1801pF @ 10V 1801pF @ 10V 220V 1801pF @ 10V 25W (Ta) 14 mOhm @ 15A, 4.5V 15°C (TJ) Surface Mount Supplier Device Package 8-SO 8-SOIC (0.154", 3.90mm Width)	Drive Voltage (Max Rds On, Min Rds On)	4.5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Power Disarrence -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	3V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs14 mOhm @ 15A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	26nC @ 5V
FET Feature - Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 14 mOhm @ 15A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Input Capacitance (Ciss) (Max) @ Vds	1801pF @ 10V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 15A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs14 mOhm @ 15A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	2.5W (Ta)
Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	14 mOhm @ 15A, 4.5V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
	Package / Case	8-SOIC (0.154", 3.90mm Width)
Report errors?		Report errors?

IRF7811AVTRPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF7811AVTRPBF Payment Methods



















IRF7811AVTRPBF Shipping Methods













If you have any question about IRF7811AVTRPBF, please do not hesitate to contact us!

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